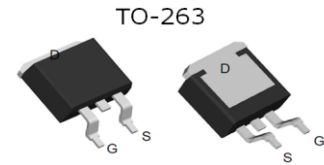


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.



Features:

- 1) $V_{DS}=-30V, I_D=-50A, R_{DS(ON)}<14m\Omega @V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	-50	A
	Continuous Drain Current- $T_C=100^\circ C$	-38	
$I_{DM (pluse)}$	Drain Current – Pulsed ^(Note 1)	-220	A
P_D	Power Dissipation- $T_C=25^\circ C$	75	W
	Power Dissipation- $T_C=100^\circ C$	37.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2	$^\circ C/W$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-30V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 25V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance	V _{GS} =-10V, I _D =-20A	---	9.5	14	m Ω
		V _{GS} =-4.5V, I _D =-15A	---	13	21	
G _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-6A	10	22	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	2350	---	pF
C _{oss}	Output Capacitance		---	380	---	
C _{rss}	Reverse Transfer Capacitance		---	285	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, I _D =-1A, R _L =15 Ω ,R _G =2.5 Ω , V _{GS} =-10V	---	11	---	ns
t _r	Rise Time		---	24	---	ns
t _{d(off)}	Turn-Off Delay Time		---	38	---	ns
t _f	Fall Time		---	10	---	ns
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _D =-12A	---	40	---	nC
Q _{gs}	Gate-Source Charge		---	7.5	---	nC
Q _{gd}	Gate-Drain Charge		---	10	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =-6A	---	---	-1.2	V

I_{SD}	Continuous Source Current	---	---	---	-55	A
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Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

Typical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Figure1. Power Dissipation

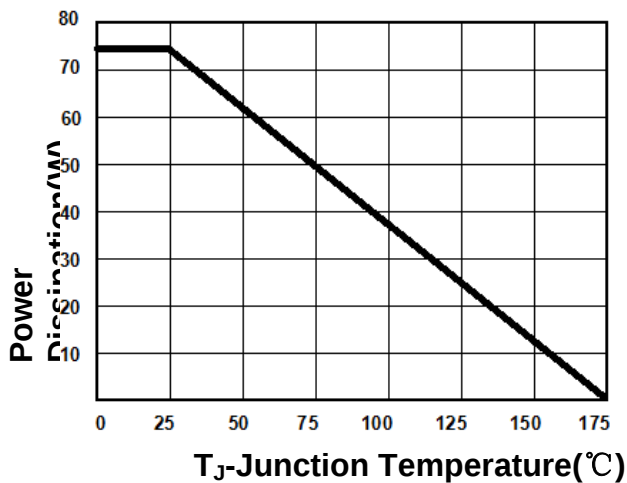


Figure2. Drain Current

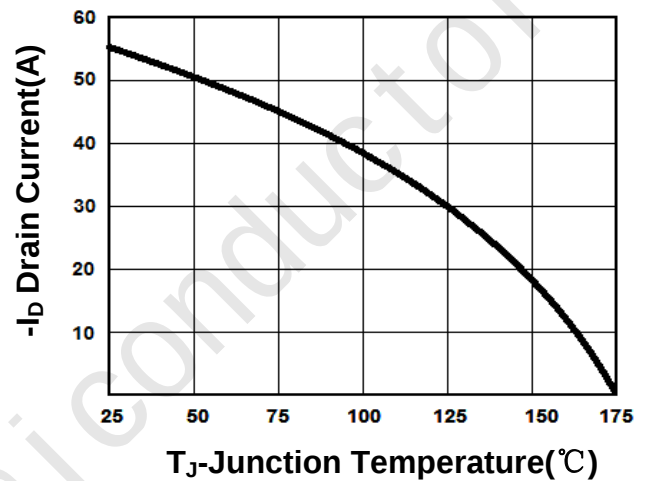


Figure3. Output Characteristics

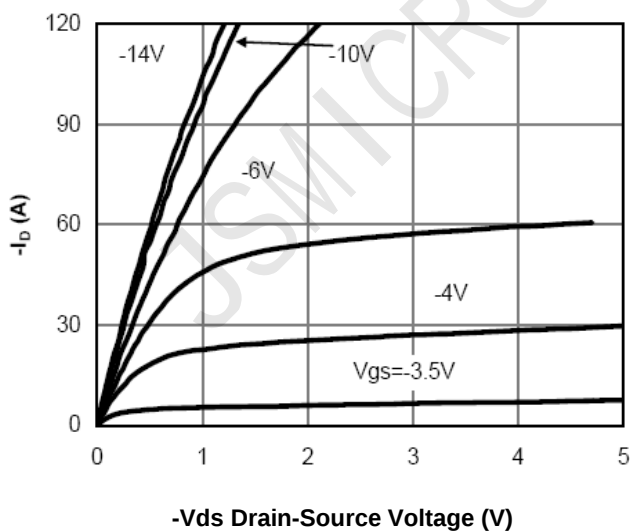


Figure4. Transfer Characteristics

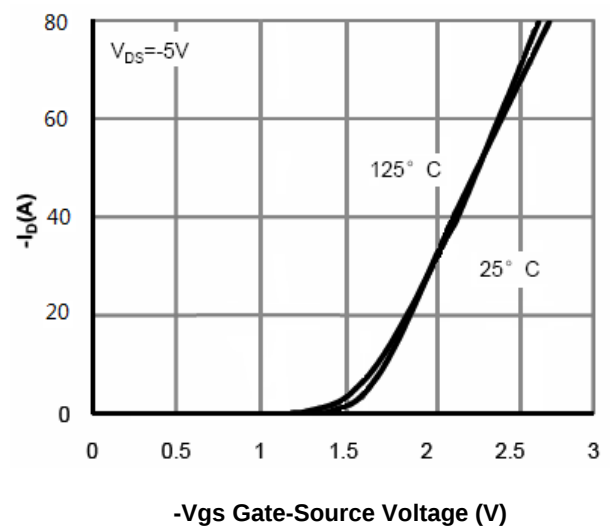


Figure5. Capacitance

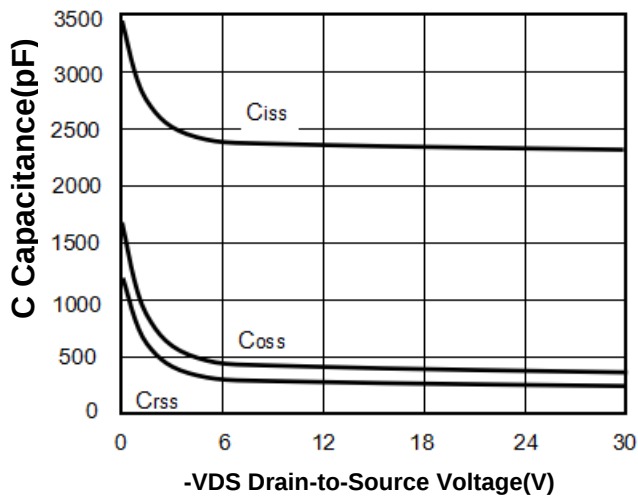
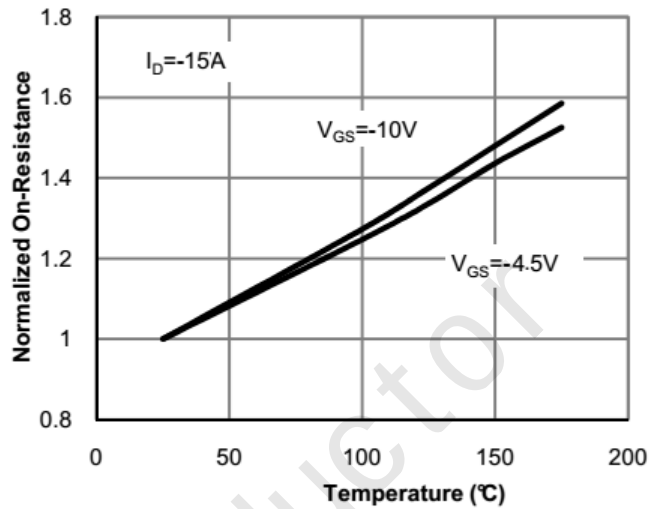
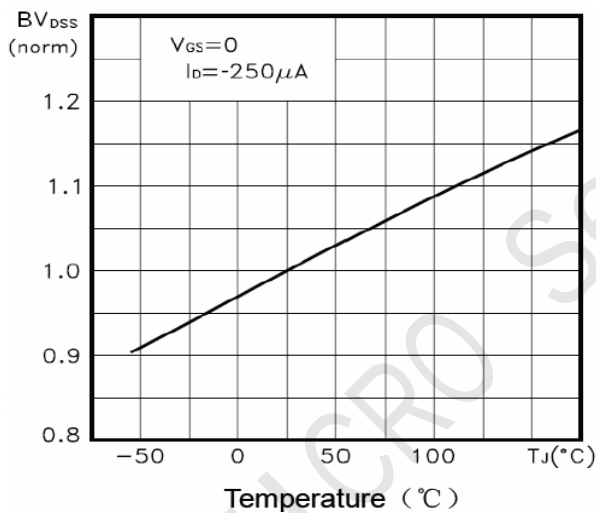
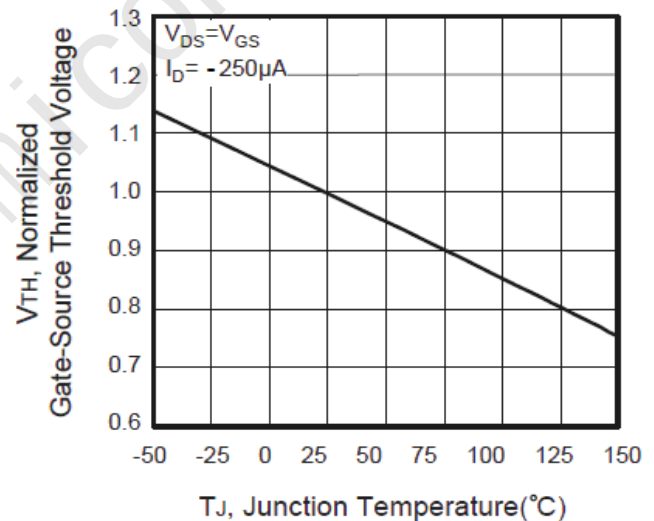

Figure6. $r_{DS(ON)}$

Figure7. Max BV_{DSS} vs Junction Temperature

Figure8. $V_{GS(th)}$ vs Junction Temperature


Figure9. Gate Charge Waveforms

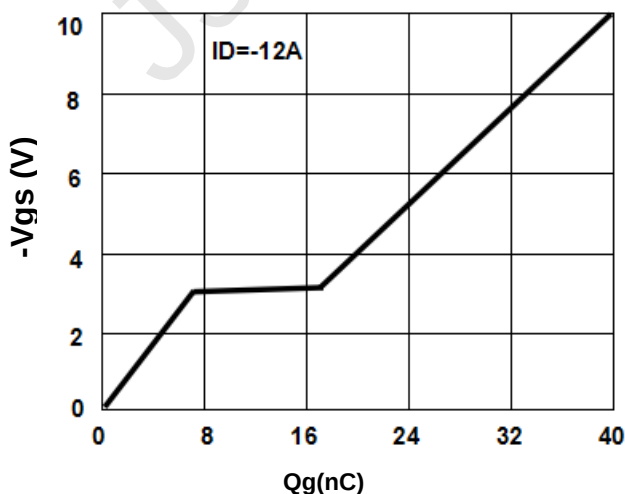


Figure10. Maximum Safe Operating Area

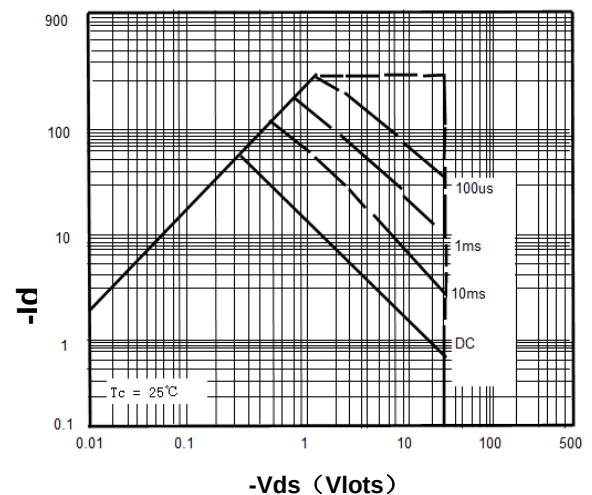
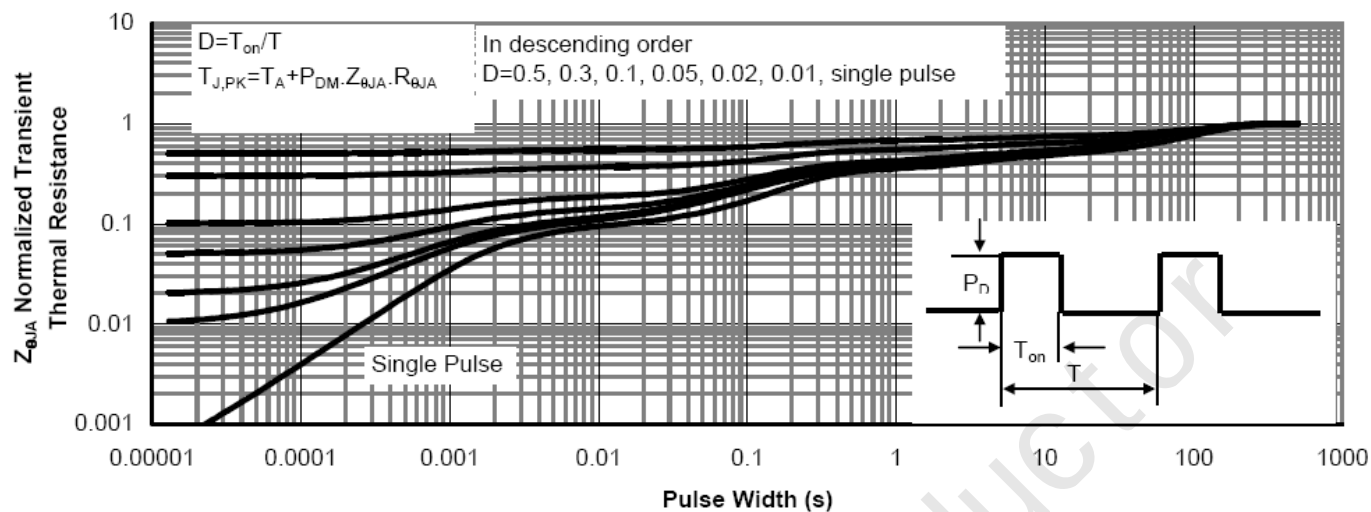
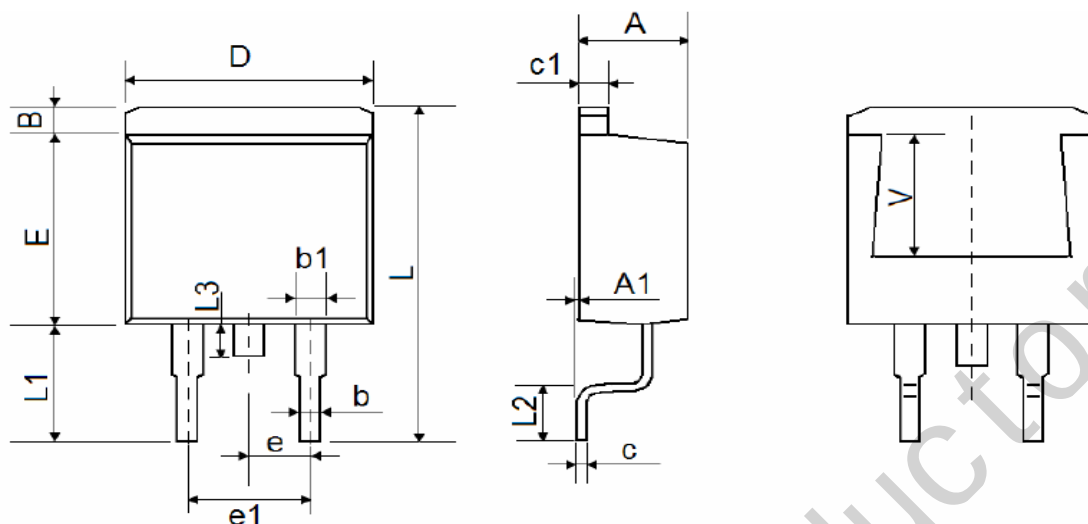


Figure11. Normalized Maximum Transient Thermal Impedance



Package Outline: TO-263


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.80	0.173	0.189
A1	0.00	0.15	0.000	0.006
B	1.17	1.37	0.046	0.054
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.31	0.53	0.012	0.021
c1	1.17	1.37	0.046	0.054
D	10.01	10.31	0.394	0.406
E	8.50	8.90	0.335	0.350
e	2.54 BSC.		0.100 BSC.	
e1	4.98	5.18	0.196	0.204
L	15.05	15.45	0.593	0.608
L1	5.08	5.48	0.200	0.216
L2	2.34	2.74	0.092	0.108
L3	1.30	1.70	0.051	0.067
V	5.600 Ref.		0.220 Ref.	